# **PUB4753** (PU7457)

## Silicon N-Channel Power F-MOS FET (with built-in zener diode)

### ■ Features

- High avalanche energy capacity
- High electrostatic breakdown voltage
- No secondary breakdown
- High breakdown voltage, large allowable power dissipation
- Allowing Low-voltage drive

## Applications

- Contactless relay
- Diving circuit for a solenoid
- Driving circuit for a motor
- Control equipment
- Switching power supply

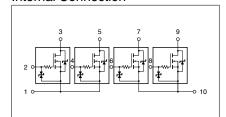
## ■ Absolute Maximum Ratings (T<sub>C</sub> = 25°C)

| Parameter                         |                     | Symbol           | Ratings     | Unit |  |
|-----------------------------------|---------------------|------------------|-------------|------|--|
| Drain to Source breakdown voltage |                     | V <sub>DSS</sub> | 100 ± 15    | V    |  |
| Gate to Source voltage            |                     | $V_{GSS}$        | ±20         | V    |  |
| Drain current                     | DC                  | $I_D$            | ±3          | A    |  |
|                                   | Pulse               | $I_{DP}$         | ±9          | A    |  |
| Avalanche energy capacity         | Non repetition      | EAS*             | 22.5        | mJ   |  |
| Allowable power                   | $T_C = 25^{\circ}C$ | D                | 15          | W    |  |
| dissipation                       | Ta = 25°C           | $P_{\rm D}$      | 3.5         |      |  |
| Channel temperature               |                     | T <sub>ch</sub>  | 150         | °C   |  |
| Storage temperature               |                     | T <sub>stg</sub> | -55 to +150 | °C   |  |

<sup>\*</sup> L = 5mH,  $I_L = 3A$ , 1 pulse

# Unit: mm 25.3±0.2 40±0.2 10.5±0.15 10.5±0.15 9X2.54=22.86±0.25 G: Gate D: Drain S: Source 10-Lead Plastic SIL Package

## Internal Connection

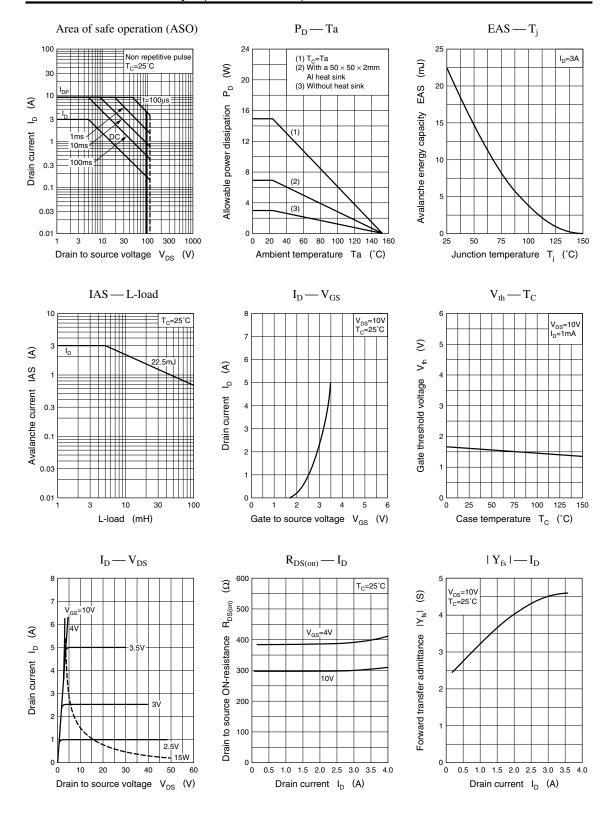


## ■ Electrical Characteristics ( $T_C = 25$ °C)

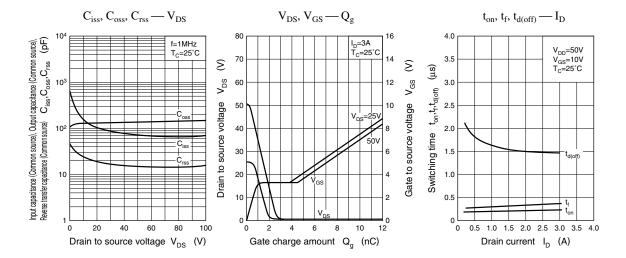
| Parameter                                    | Symbol               | Conditions  | min | typ | max  | Unit |
|--|----------------------|---|-----|-----|------|------|
| Drain to Source cut-off current              | $I_{DSS}$            | $V_{DS} = 80V, V_{GS} = 0$                              |     |     | 10   | μA   |
| Gate to Source leakage current               | $I_{GSS}$            | $V_{GS} = \pm 20V, V_{DS} = 0$                          |     |     | ±10  | μA   |
| Drain to Source breakdown voltage            | $V_{\rm DSS}$        | $I_D = 1 \text{mA}, V_{GS} = 0$                         | 85  |     | 115  | V    |
| Gate threshold voltage                       | $V_{th}$             | $V_{DS} = 10V$ , $I_D = 1mA$                            | 1   |     | 2.5  | V    |
| Drain to Source ON-resistance                | R <sub>DS(on)1</sub> | $V_{GS} = 10V, I_D = 2A$                                |     | 300 | 450  | mΩ   |
|  | R <sub>DS(on)2</sub> | $V_{GS} = 4V$ , $I_D = 2A$                              |     | 400 | 600  | mΩ   |
| Forward transfer admittance                  | Y <sub>fs</sub>      | $V_{DS} = 10V, I_D = 2A$                                | 2.5 | 4   |      | S    |
| Diode forward voltage                        | V <sub>DSF</sub>     | $I_{DR} = 3A, V_{GS} = 0$                               |     |     | -1.6 | V    |
| Input capacitance (Common Source)            | C <sub>iss</sub>     | $V_{DS} = 10V, V_{GS} = 0, f = 1MHz$                    |     | 130 |      | pF   |
| Output capacitance (Common Source)           | Coss                 |   |     | 160 |      | pF   |
| Reverse transfer capacitance (Common Source) | C <sub>rss</sub>     |   |     | 25  |      | pF   |
| Turn-on time                                 | t <sub>on</sub>      | $V_{GS} = 10V, I_D = 2A$ $V_{DD} = 50V, R_L = 25\Omega$ |     | 0.2 |      | μs   |
| Fall time                                    | $t_{\rm f}$          |   |     | 0.3 |      | μs   |
| Turn-off time (delay time)                   | t <sub>d(off)</sub>  |   |     | 1.5 |      | μs   |

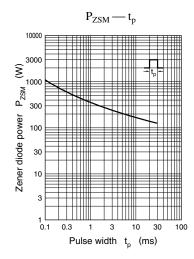
Note) The part number in the parenthesis shows conventional part number.

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